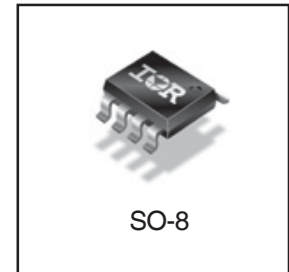
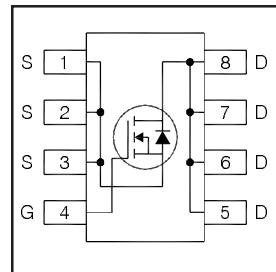


# IRL6342PbF

HEXFET® Power MOSFET

$V_{DS}$	<b>30</b>	<b>V</b>
$V_{GS}$	<b>±12</b>	<b>V</b>
$R_{DS(on) \max}$ (@ $V_{GS} = 4.5V$ )	<b>14.6</b>	<b>mΩ</b>
$Q_g$ (typical)	<b>11</b>	<b>nC</b>
$I_D$ (@ $T_A = 25^\circ C$ )	<b>9.9</b>	<b>A</b>



## Applications

- Battery operated DC motor inverter MOSFET
- System/Load Switch

## Features and Benefits

### Features

Industry-Standard SO-8 Package
RoHS Compliant Containing no Lead, no Bromide and no Halogen
MSL1, Consumer Qualification

⇒

### Resulting Benefits

Multi-Vendor Compatibility
Environmentally Friendlier
Increased Reliability

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRL6342PBF	SO-8	Tube/Bulk	95	
IRL6342TRPBF	SO-8	Tape and Reel	4000	

## Absolute Maximum Ratings

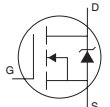
	Parameter	Max.	Units
$V_{DS}$	Drain-to-Source Voltage	30	V
$V_{GS}$	Gate-to-Source Voltage	±12	
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	9.9	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	7.9	
$I_{DM}$	Pulsed Drain Current ①	79	
$P_D @ T_A = 25^\circ C$	Power Dissipation ③	2.5	W
$P_D @ T_A = 70^\circ C$	Power Dissipation ③	1.6	
	Linear Derating Factor	0.02	W/°C
$T_J$	Operating Junction and	-55 to + 150	°C
$T_{STG}$	Storage Temperature Range		

Notes ① through ④ are on page 2

### Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$BV_{DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	22	—	mV/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	12.0	14.6	mΩ	$V_{GS} = 4.5V, I_D = 9.9A$ ②
		—	15.0	19.0		$V_{GS} = 2.5V, I_D = 7.9A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	0.5	—	1.1	V	$V_{DS} = V_{GS}, I_D = 10\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-4.2	—	mV/°C	
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 12V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -12V$
$g_{fs}$	Forward Transconductance	38	—	—	S	$V_{DS} = 10V, I_D = 7.9A$
$Q_g$	Total Gate Charge	—	11	—	nC	$V_{GS} = 4.5V$ $V_{DS} = 15V$ $I_D = 7.9A$
$Q_{gs1}$	Pre-V <sub>th</sub> Gate-to-Source Charge	—	0.01	—		
$Q_{gs2}$	Post-V <sub>th</sub> Gate-to-Source Charge	—	0.60	—		
$Q_{gd}$	Gate-to-Drain Charge	—	4.6	—		
$Q_{godr}$	Gate Charge Overdrive	—	5.79	—		
$Q_{sw}$	Switch Charge ( $Q_{gs2} + Q_{gd}$ )	—	5.2	—		
$R_G$	Gate Resistance	—	2.0	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	6.0	—	ns	$V_{DD} = 15V, V_{GS} = 4.5V$ ③ $I_D = 7.9A$ $R_G = 6.8\Omega$ See Figs. 18
$t_r$	Rise Time	—	12	—		
$t_{d(off)}$	Turn-Off Delay Time	—	33	—		
$t_f$	Fall Time	—	14	—		
$C_{iss}$	Input Capacitance	—	1025	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0MHz$
$C_{oss}$	Output Capacitance	—	97	—		
$C_{rss}$	Reverse Transfer Capacitance	—	70	—		

### Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	79		
$V_{SD}$	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}, I_S = 9.9A, V_{GS} = 0V$ ②
$t_{rr}$	Reverse Recovery Time	—	13	20	ns	$T_J = 25^\circ\text{C}, I_F = 7.9A, V_{DD} = 24V$
$Q_{rr}$	Reverse Recovery Charge	—	5.2	7.8	nC	$di/dt = 100/\mu s$ ②

### Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead ④	—	20	°C/W
$R_{\theta JA}$	Junction-to-Ambient ③	—	50	

#### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width  $\leq 400\mu s$ ; duty cycle  $\leq 2\%$ .
- ③ When mounted on 1 inch square copper board.
- ④  $R_{\theta}$  is measured at  $T_J$  of approximately  $90^\circ\text{C}$ .

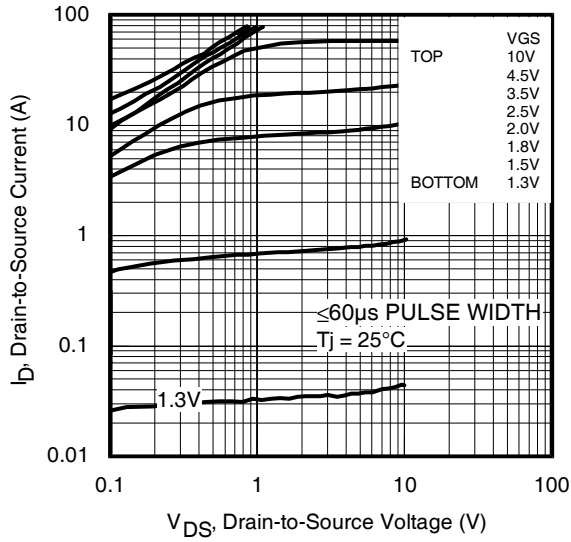


Fig 1. Typical Output Characteristics

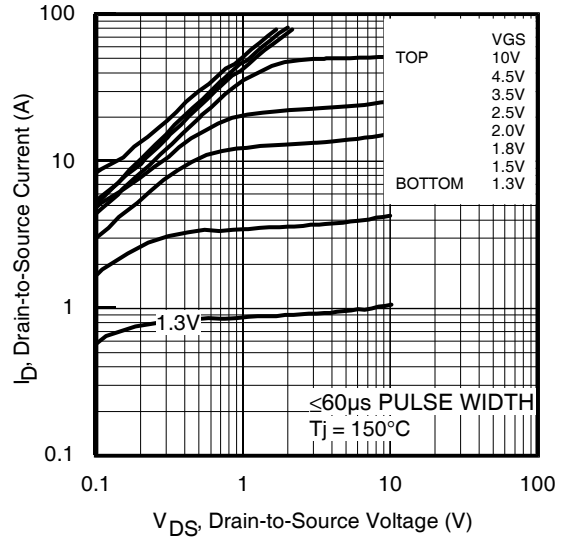


Fig 2. Typical Output Characteristics

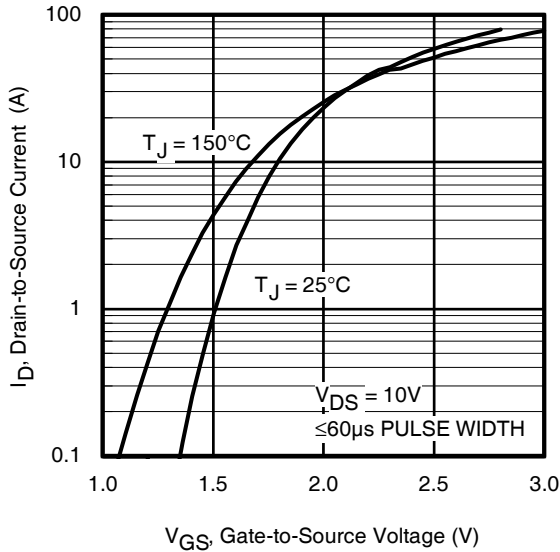


Fig 3. Typical Transfer Characteristics

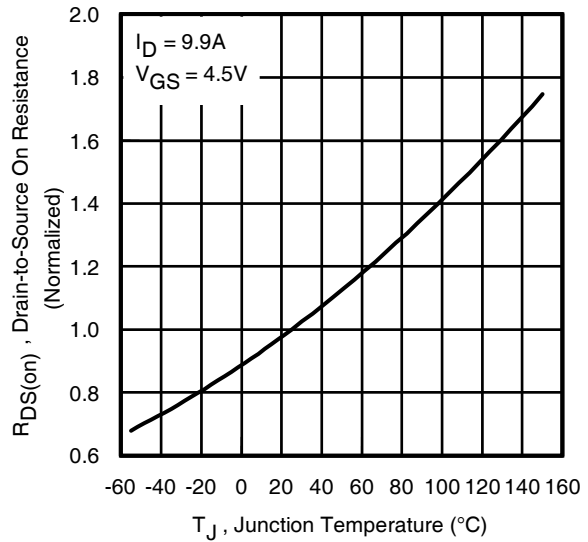


Fig 4. Normalized On-Resistance vs. Temperature

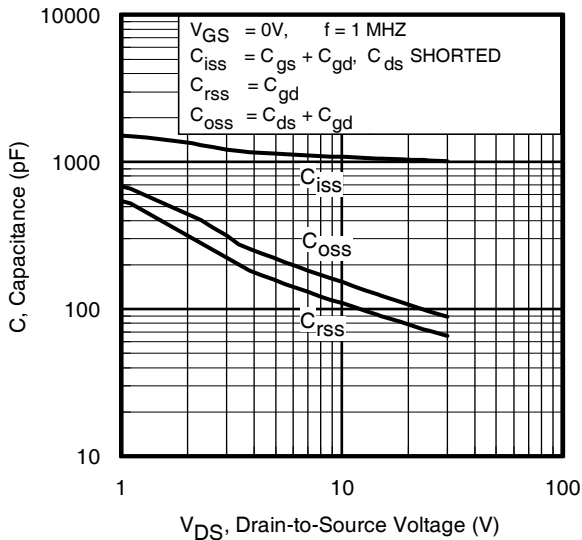


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage  
www.irf.com

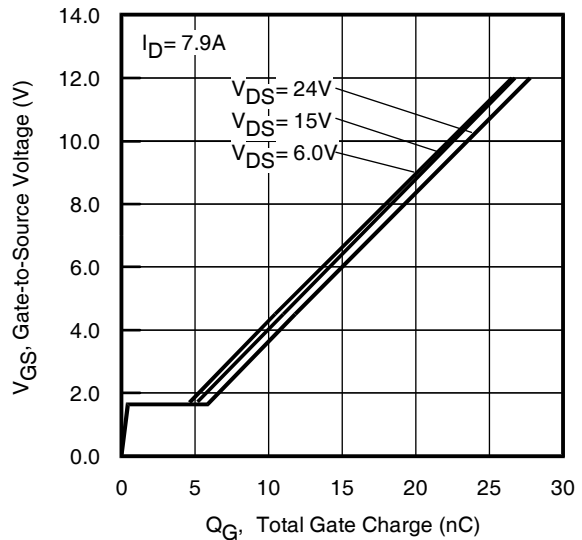
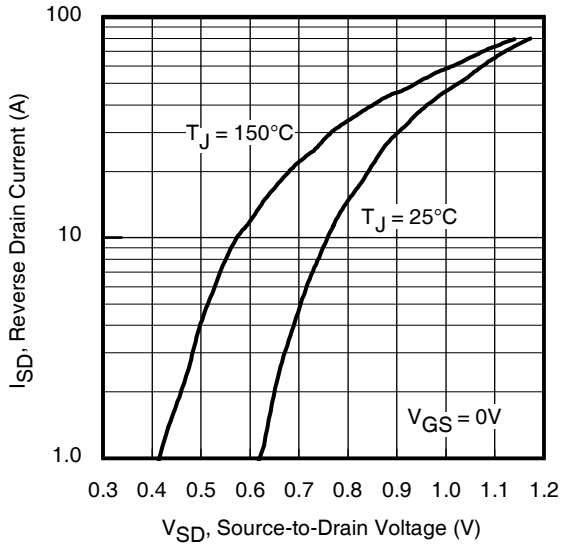
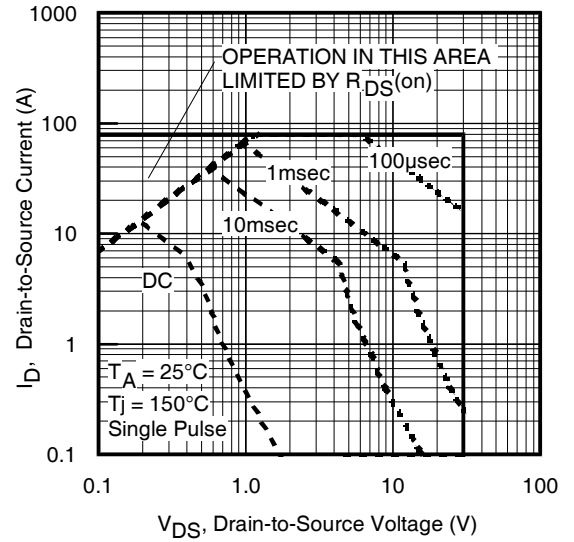


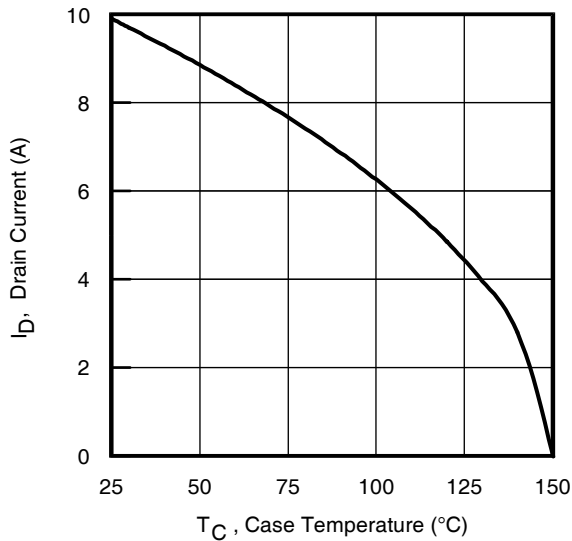
Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage



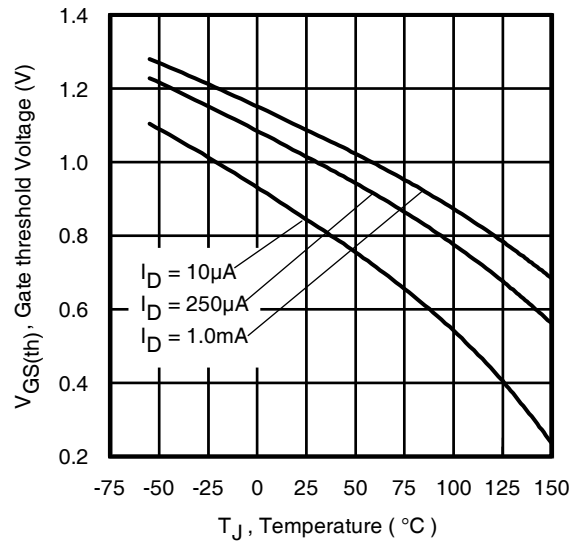
**Fig 7.** Typical Source-Drain Diode Forward Voltage



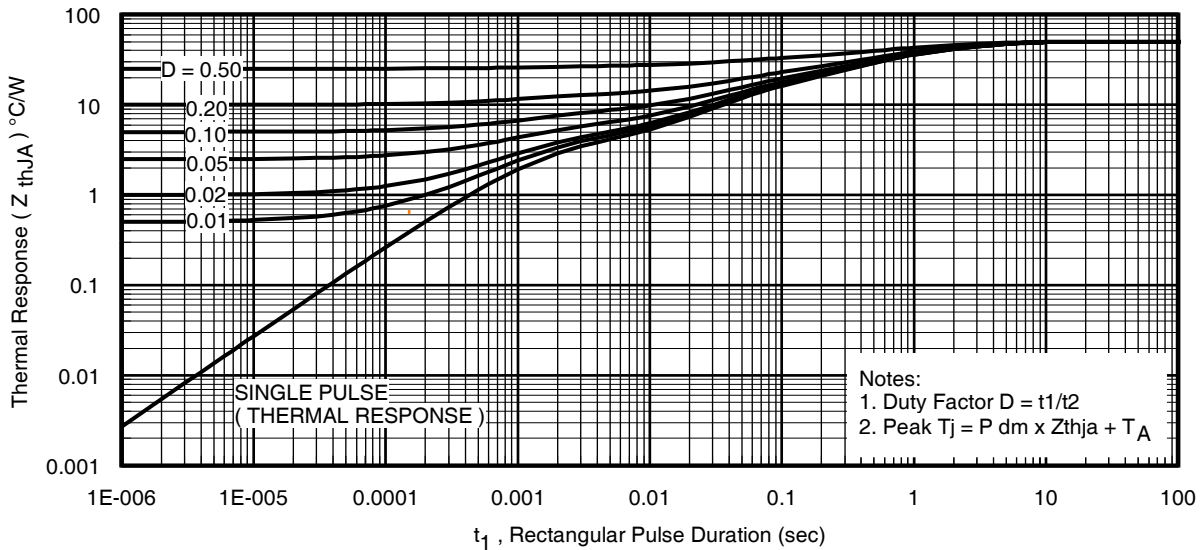
**Fig 8.** Maximum Safe Operating Area



**Fig 9.** Maximum Drain Current vs. Case (Bottom) Temperature



**Fig 10.** Threshold Voltage vs. Temperature



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case (Bottom)

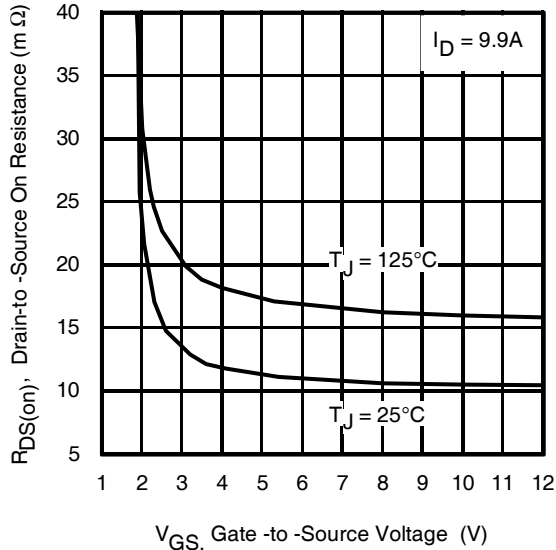


Fig 12. On-Resistance vs. Gate Voltage

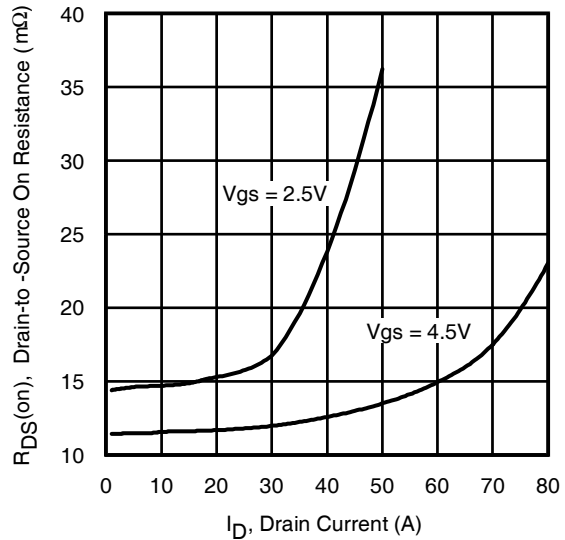


Fig 13. Typical On-Resistance vs. Drain Current

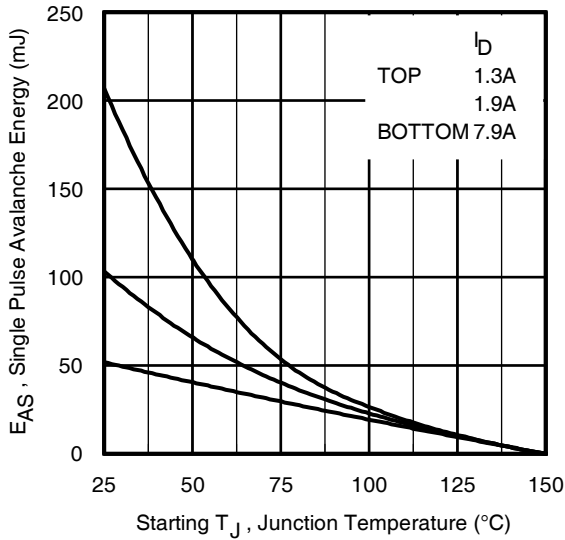


Fig 14. Maximum Avalanche Energy vs. Drain Current

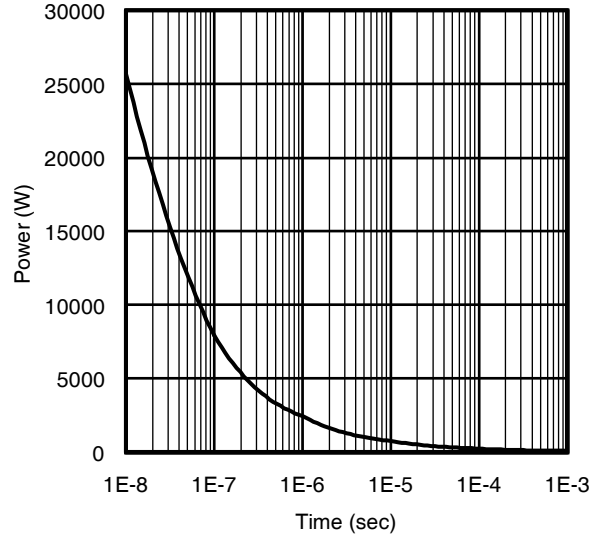


Fig 15. Typical Power vs. Time

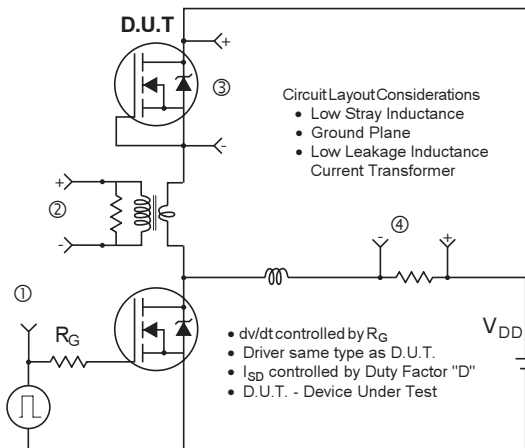
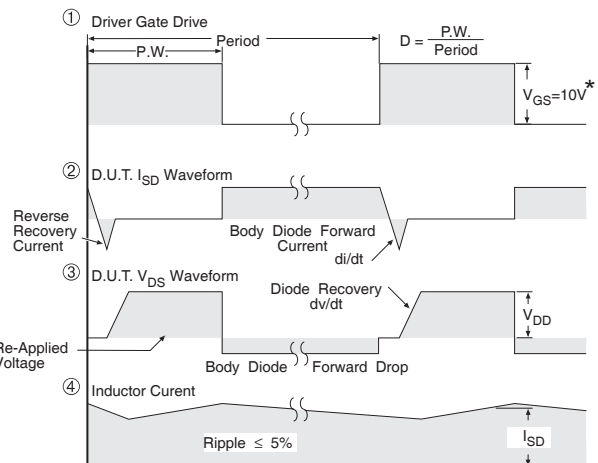
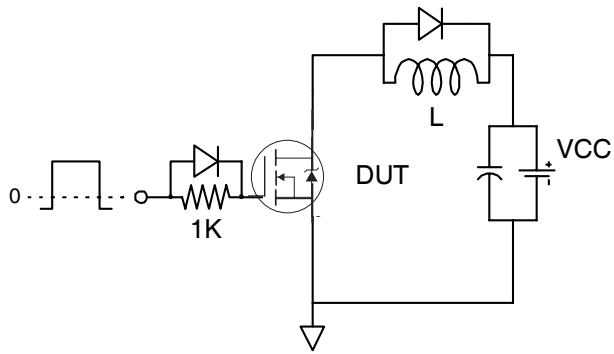


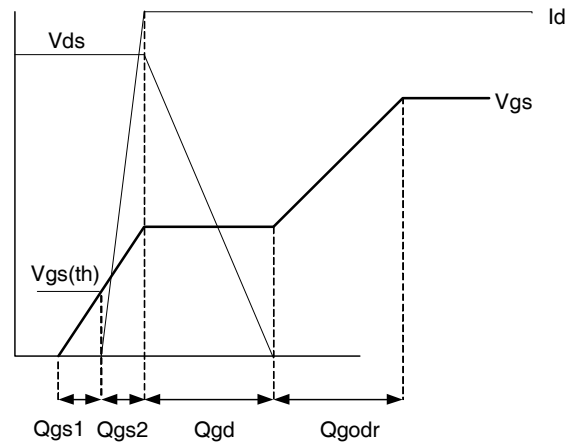
Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel  
HEXFET® Power MOSFETs



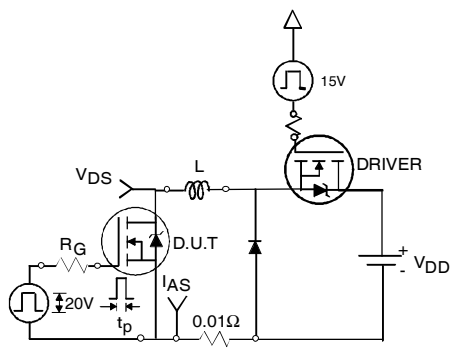
\*  $V_{GS} = 5V$  for Logic Level Devices



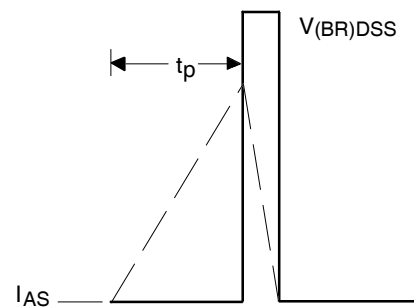
**Fig 17a.** Gate Charge Test Circuit



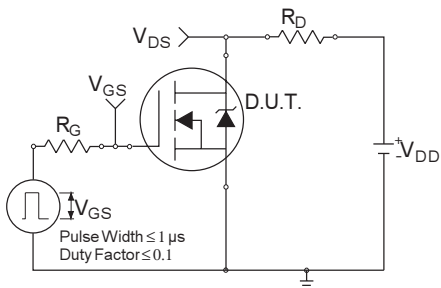
**Fig 17b.** Gate Charge Waveform



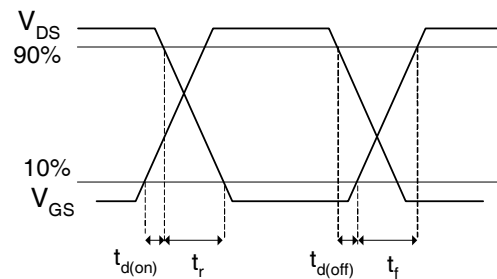
**Fig 18a.** Unclamped Inductive Test Circuit



**Fig 18b.** Unclamped Inductive Waveforms



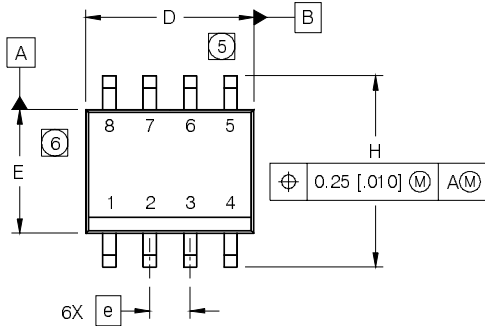
**Fig 19a.** Switching Time Test Circuit



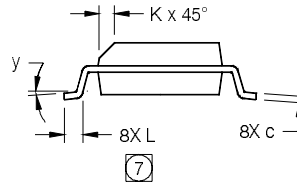
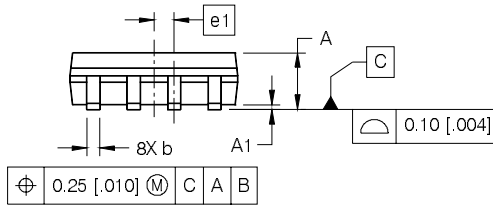
**Fig 19b.** Switching Time Waveforms

## SO-8 Package Outline (Mosfet & Fetky)

Dimensions are shown in millimeters (inches)



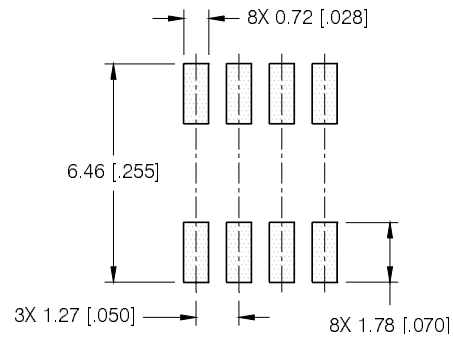
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



**NOTES:**

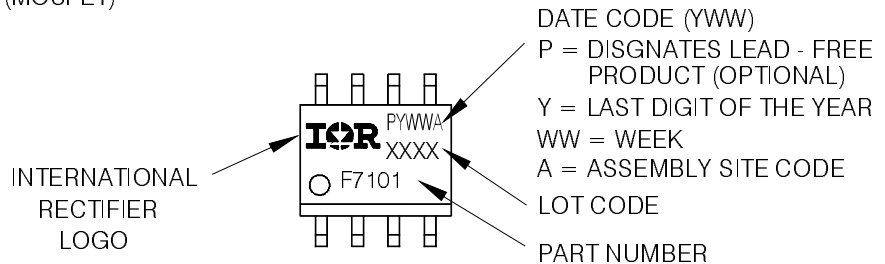
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

**FOOTPRINT**



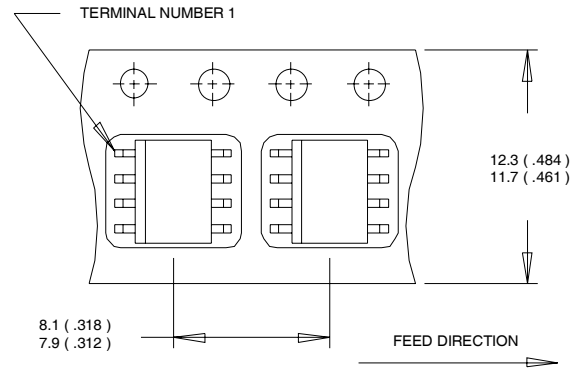
## SO-8 Part Marking Information

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

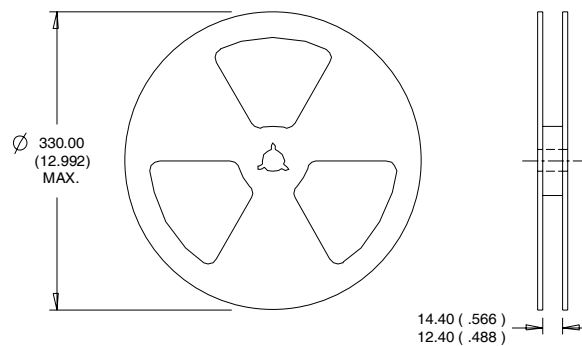


Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

## SO-8 Tape and Reel



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

### Qualification information<sup>†</sup>

Qualification level	Consumer <sup>††</sup> (per JEDEC JESD47F <sup>†††</sup> guidelines )	
Moisture Sensitivity Level	SO-8	MSL1 (per JEDEC J-STD-020D <sup>†††</sup> )
RoHS compliant	Yes	

<sup>†</sup> Qualification standards can be found at International Rectifier's web site  
<http://www.irf.com/product-info/reliability>

<sup>††</sup> Higher qualification ratings may be available should the user have such requirements.  
Please contact your International Rectifier sales representative for further information:  
<http://www.irf.com/whoto-call/salesrep/>

<sup>†††</sup> Applicable version of JEDEC standard at the time of product release.

Data and specifications subject to change without notice.

International  
**IR** Rectifier

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